

M393T2863FBA
M393T5663FBA
M393T5660FBA
M393T5160FBA

240pin Registered DIMM based on 1Gb F-die

60 FBGA with Lead-Free & Halogen-Free
(RoHS compliant)

datasheet

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[Revision History](#)

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1. DDR2 Unbuffered DIMM Ordering Information

Part Number	Density	Organization	Component Composition	Number of Rank	Height
M393T2863FBA-CE7/F7/E6	1GB	128Mx72	128Mx8(K4T1G084QF)*9	1	30mm
M393T5663FBA-CE7/F7/E6	2GB	256Mx72	128Mx8(K4T1G084QF)*18	2	30mm
M393T5660FBA-CE7/F7/E6	2GB	256Mx72	256Mx4(K4T1G084QF)*18	1	30mm
M393T5160FBA-CE7/F7/E6	4GB	512Mx72	256Mx4(K4T1G084QF)*36	2	30mm

NOTE :

- "B" of Part number(11th digit) stands for Lead-Free, Halogen-Free, and RoHS compliant products.
- "A" of Part number(12th digit) stands for Parity Register products.

2. Key Features

- Performance range

	E7 (DDR2-800)	F7 (DDR2-800)	E6 (DDR2-667)	Unit
CAS Latency	5	6	5	tCK
tRCD(min)	12.5	15	15	ns
tRP(min)	12.5	15	15	ns
tRC(min)	57.5	60	60	ns

- JEDEC standard $V_{DD} = 1.8V \pm 0.1V$ Power Supply
- $V_{DDQ} = 1.8V \pm 0.1V$
- 267MHz f_{CK} for 533Mb/sec/pin, 333MHz f_{CK} for 667Mb/sec/pin, 400MHz f_{CK} for 800Mb/sec/pin
- 8 Banks
- Posted \overline{CAS}
- Programmable \overline{CAS} Latency: 3, 4, 5, 6
- Programmable Additive Latency: 0, 1, 2, 3, 4, 5
- Write Latency(WL) = Read Latency(RL) - 1
- Burst Length: 4, 8(Interleave/Nibble sequential)
- Programmable Sequential / Interleave Burst Mode
- Bi-directional Differential Data-Strobe (Single-ended data-strobe is an optional feature)
- Off-Chip Driver(OCD) Impedance Adjustment
- On Die Termination with selectable values(50/75/150 ohms or disable)
- Average Refresh Period 7.8us at lower than a $T_{CASE} 85^{\circ}C$, 3.9us at $85^{\circ}C < T_{CASE} \leq 95^{\circ}C$
- Support High Temperature Self-Refresh rate enable feature
- Serial presence detect with EEPROM
- DDR2 SDRAM Package: 60ball FBGA(Flip-chip) - 256Mx4/128Mx8
- All of products are Lead-Free, Halogen-Free, and RoHS compliant

NOTE : For detailed DDR2 SDRAM operation, please refer to Samsung's Device operation & Timing diagram.

3. Address Configuration

Organization	Row Address	Column Address	Bank Address	Auto Precharge
256Mx4(1Gb) based Module	A0-A13	A0-A9, A11	BA0-BA2	A10
128Mx8(1Gb) based Module	A0-A13	A0-A9	BA0-BA2	A10

4. Pin Configurations (Front side/Back side)

Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back
1	V _{REF}	121	V _{SS}	31	DQ19	151	V _{SS}	61	A4	181	V _{DDQ}	91	V _{SS}	211	DM5/DQS14
2	V _{SS}	122	DQ4	32	V _{SS}	152	DQ28	62	V _{DDQ}	182	A3	92	DQS5	212	NC/DQS14
3	DQ0	123	DQ5	33	DQ24	153	DQ29	63	A2	183	A1	93	DQS5	213	V _{SS}
4	DQ1	124	V _{SS}	34	DQ25	154	V _{SS}	64	V _{DD}	184	V _{DD}	94	V _{SS}	214	DQ46
5	V _{SS}	125	DM0/DQS9	35	V _{SS}	155	DM3/DQS12	KEY				95	DQ42	215	DQ47
6	DQS0	126	NC/DQS9	36	DQS3	156	NC/DQS12	65	V _{SS}	185	CK0	96	DQ43	216	V _{SS}
7	DQS0	127	V _{SS}	37	DQS3	157	V _{SS}	66	V _{SS}	186	CK0	97	V _{SS}	217	DQ52
8	V _{SS}	128	DQ6	38	V _{SS}	158	DQ30	67	V _{DD}	187	V _{DD}	98	DQ48	218	DQ53
9	DQ2	129	DQ7	39	DQ26	159	DQ31	68	NC/Par_In	188	A0	99	DQ49	219	V _{SS}
10	DQ3	130	V _{SS}	40	DQ27	160	V _{SS}	69	V _{DD}	189	V _{DD}	100	V _{SS}	220	S2
11	V _{SS}	131	DQ12	41	V _{SS}	161	CB4	70	A10/AP	190	BA1	101	SA2	221	S3
12	DQ8	132	DQ13	42	CB0	162	CB5	71	BA0	191	V _{DDQ}	102	NC(TEST)	222	V _{SS}
13	DQ9	133	V _{SS}	43	CB1	163	V _{SS}	72	V _{DDQ}	192	RAS	103	V _{SS}	223	DM6/DQS15
14	V _{SS}	134	DM1/DQS10	44	V _{SS}	164	DM8/DQS17	73	WE	193	S0	104	DQS6	224	NC/DQS15
15	DQS1	135	NC/DQS10	45	DQS8	165	NC/DQS17	74	CAS	194	V _{DDQ}	105	DQS6	225	V _{SS}
16	DQS1	136	V _{SS}	46	DQS8	166	V _{SS}	75	V _{DDQ}	195	ODT0	106	V _{SS}	226	DQ54
17	V _{SS}	137	RFU	47	V _{SS}	167	CB6	76	S1	196	A13	107	DQ50	227	DQ55
18	RESET	138	RFU	48	CB2	168	CB7	77	ODT1	197	V _{DD}	108	DQ51	228	V _{SS}
19	NC	139	V _{SS}	49	CB3	169	V _{SS}	78	V _{DDQ}	198	V _{SS}	109	V _{SS}	229	DQ60
20	V _{SS}	140	DQ14	50	V _{SS}	170	V _{DDQ}	79	V _{SS}	199	DQ36	110	DQ56	230	DQ61
21	DQ10	141	DQ15	51	V _{DDQ}	171	CKE1	80	DQ32	200	DQ37	111	DQ57	231	V _{SS}
22	DQ11	142	V _{SS}	52	CKE0	172	V _{DD}	81	DQ33	201	V _{SS}	112	V _{SS}	232	DM7/DQS16
23	V _{SS}	143	DQ20	53	V _{DD}	173	NC	82	V _{SS}	202	DM4/DQS13	113	DQS7	233	NC/DQS16
24	DQ16	144	DQ21	54	BA2	174	NC	83	DQS4	203	NC/DQS13	114	DQS7	234	V _{SS}
25	DQ17	145	V _{SS}	55	NC/Err_Out	175	V _{DDQ}	84	DQS4	204	V _{SS}	115	V _{SS}	235	DQ62
26	V _{SS}	146	DM2/DQS11	56	V _{DDQ}	176	A12	85	V _{SS}	205	DQ38	116	DQ58	236	DQ63
27	DQS2	147	NC/DQS11	57	A11	177	A9	86	DQ34	206	DQ39	117	DQ59	237	V _{SS}
28	DQS2	148	V _{SS}	58	A7	178	V _{DD}	87	DQ35	207	V _{SS}	118	V _{SS}	238	V _{DDSPD}
29	V _{SS}	149	DQ22	59	V _{DD}	179	A8	88	V _{SS}	208	DQ44	119	SDA	239	SA0
30	DQ18	150	DQ23	60	A5	180	A6	89	DQ40	209	DQ45	120	SCL	240	SA1
								90	DQ41	210	V _{SS}				

NOTE : NC = No Connect, RFU = Reserved for Future Use

1. RESET (Pin 18) is connected to both OE of PLL and Reset of register.
2. The Test pin (Pin 102) is reserved for bus analysis probes and is not connected on normal memory modules (DIMMs)
3. NC/Err_Out (Pin 55) and NC/Par_In (Pin 68) are for optional function to check address and command parity.

5. Pin Description

Pin Name	Description	Pin Name	Description
CK0	Clock Inputs, positive line	ODT0~ODT1	On die termination
CK0	Clock inputs, negative line	DQ0~DQ63	Data Input/Output
CKE0, CKE1	Clock Enables	CB0~CB7	Data check bits Input/Output
RAS	Row Address Strobe	DQS0~DQS8	Data strobes
CAS	Column Address Strobe	DQS0~DQS8	Data strobes, negative line
WE	Write Enable	DM(0~8),DQS(9~17)	Data Masks / Data strobes (Read)
S0~ S3	Chip Selects	DQS9~DQS17	Data strobes (Read), negative line
A0~A9, A11~A13	Address Inputs	RFU	Reserved for Future Use
A10/AP	Address Input/Autoprecharge	NC	No Connect
BA0~BA2	DDR2 SDRAM Bank Address	TEST	Memory bus test tool (Not Connect and Not Useable on DIMMs)
SCL	Serial Presence Detect (SPD) Clock Input	V _{DD}	Core Power
SDA	SPD Data Input/Output	V _{DDQ}	I/O Power
SA0~SA2	SPD address	V _{SS}	Ground
Par_In	Parity bit for the Address and Control bus	V _{REF}	Input/Output Reference
Err_Out	Parity error found in the Address and Control bus	V _{DDSPD}	SPD Power
RESET	Register and PLL control pin		

* The V_{DD} and V_{DDQ} pins are tied to the single power-plane on PCB.



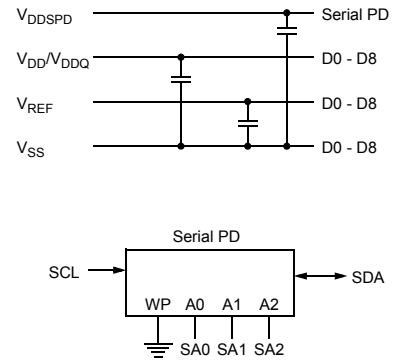
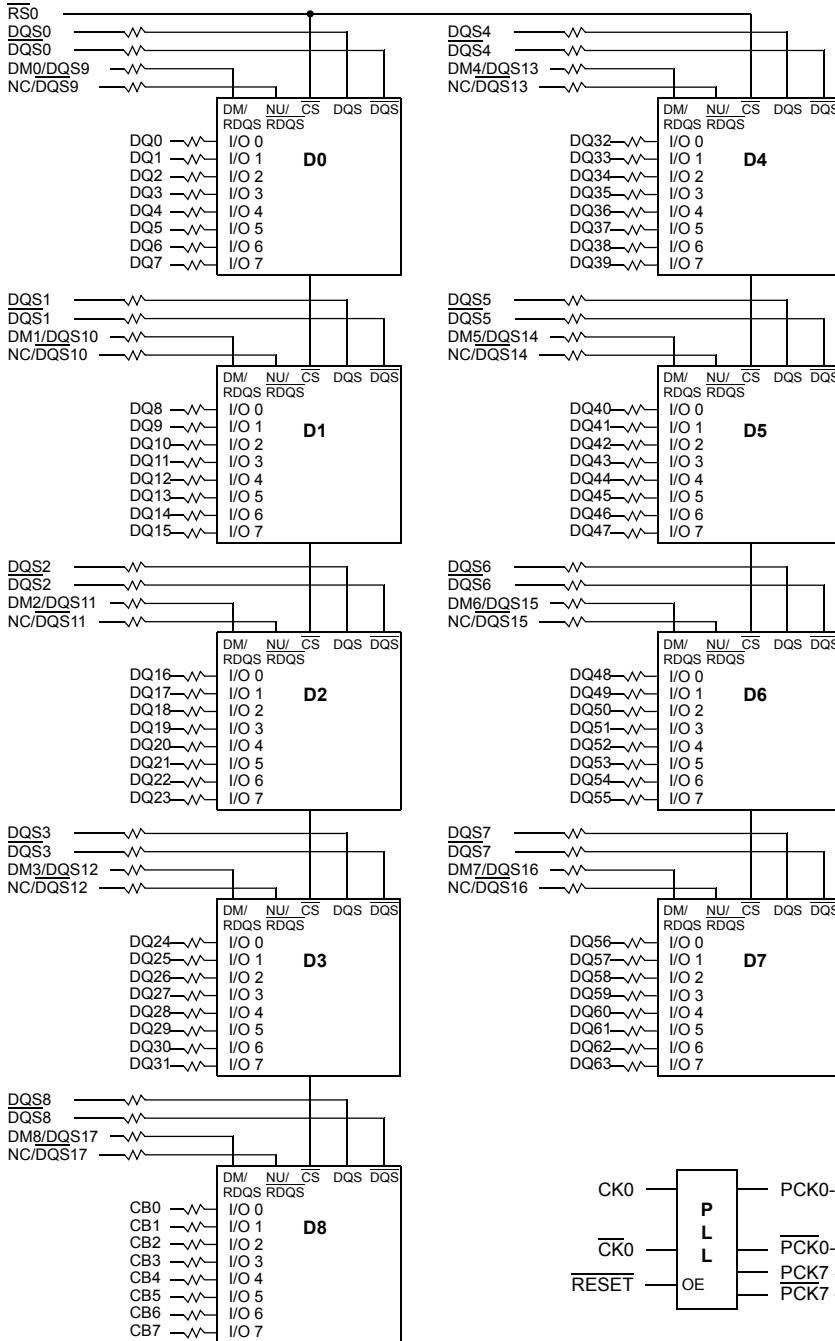
6. Input/Output Function Description

Symbol	Type	Description
CK0	Input	Positive line of the differential pair of system clock inputs that drives input to the on-DIMM PLL.
$\overline{\text{CK0}}$	Input	Negative line of the differential pair of system clock inputs that drives the input to the on-DIMM PLL.
CKE0~CKE1	Input	Activates the SDRAM CK signal when high and deactivates the CK signal when low. By deactivating the clocks, CKE low initiates the Power Down mode, or the Self Refresh mode.
$\overline{\text{S0}}\sim\overline{\text{S3}}$	Input	Enables the associated SDRAM command decoder when low and disables decoder when high. When decoder is disabled, new commands are ignored but previous operations continue. These input signals also disable all outputs (except CKE and ODT) of the register(s) on the DIMM when both inputs are high.
ODT0~ODT1	Input	I/O bus impedance control signals.
$\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$	Input	When sampled at the positive rising edge of the clock, $\overline{\text{CAS}}$, $\overline{\text{RAS}}$, and $\overline{\text{WE}}$ define the operation to be executed by the SDRAM.
V _{REF}	Supply	Reference voltage for SSTL_18 inputs
V _{DDQ}	Supply	Isolated power supply for the DDR SDRAM output buffers to provide improved noise immunity
BA0~BA2	Input	Selects which SDRAM bank of eight is activated.
A0~A9,A10/AP A11~A13	Input	During a Bank Activate command cycle, Address defines the row address. During a Read or Write command cycle, Address defines the column address. In addition to the column address, AP is used to invoke autoprecharge operation at the end of the burst read or write cycle. If AP is high, autoprecharge is selected and BA0, BA1, BA2 defines the bank to be precharged. If AP is low, autoprecharge is disabled. During a Pre-charge command cycle, AP is used in conjunction with BA0, BA1, BA2 to control which bank(s) to precharge. If AP is high, all banks will be precharged regardless of the state of BA0 or BA1 or BA2. If AP is low, BA0 and BA1 and BA2 are used to define which bank to precharge.
DQ0~63, CB0~CB7	In/Out	Data and Check Bit Input/Output pins
DM0~DM8	Input	Masks write data when high, issued concurrently with input data. Both DM and DQ have a write latency of one clock once the write command is registered into the SDRAM.
V _{DD} , V _{SS}	Supply	Power and ground for the DDR SDRAM input buffers and core logic
DQS0~DQS17	In/Out	Positive line of the differential data strobe for input and output data.
$\overline{\text{DQS0}}\sim\overline{\text{DQS17}}$	In/Out	Negative line of the differential data strobe for input and output data.
SA0~SA2	Input	These signals are tied at the system planar to either V _{SS} or V _{DDSPD} to configure the serial SPD EEPROM address range.
SDA	In/Out	This bidirectional pin is used to transfer data into or out of the SPD EEPROM. A resistor must be connected from the SDA bus line to V _{DDSPD} to act as a pullup.
SCL	Input	This signal is used to clock data into and out of the SPD EEPROM. A resistor may be connected from the SCL bus time to V _{DDSPD} to act as a pullup.
V _{DDSPD}	Supply	Serial EEPROM positive power supply (wired to a separate power pin at the connector which supports from 1.7 Volt to 3.6 Volt operation).
$\overline{\text{RESET}}$	Input	The RESET pin is connected to the RST pin on the register and to the OE pin on the PLL. When low, all register outputs will be driven low and the PLL clocks to the DRAMs and register(s) will be set to low level (The PLL will remain synchronized with the input clock)
Par_In	Input	Parity bit for the Address and Control bus. ("1 " : Odd, "0 " : Even)
$\overline{\text{Err_Out}}$	Output	Parity error found in the Address and Control bus
TEST	In/Out	Used by memory bus analysis tools (unused on memory DIMMs)

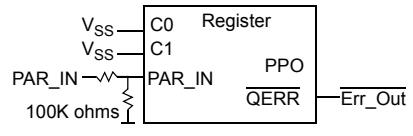
7. Functional Block Diagram :

7.1 1GB, 128Mx72 Module - M393T2863FBA

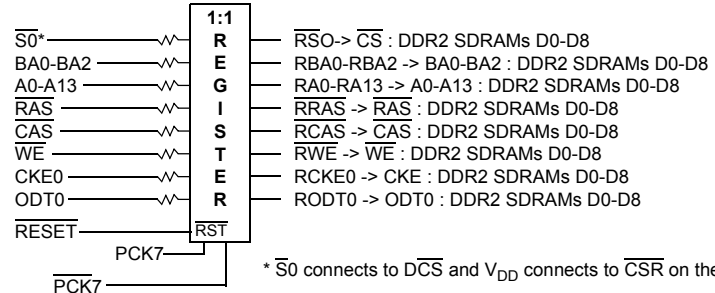
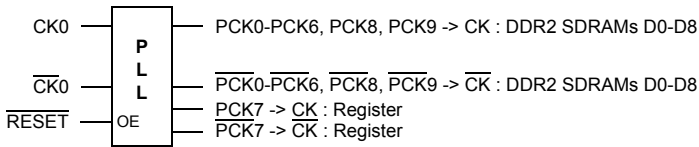
(Populated as 1 rank of x8 DDR2 SDRAMs)



Signals for Address and Command Parity Function



The resistors on Par_In, A14, A15, and the signal line of Err_Out refer to the section: "Register Options for Unused Address inputs"

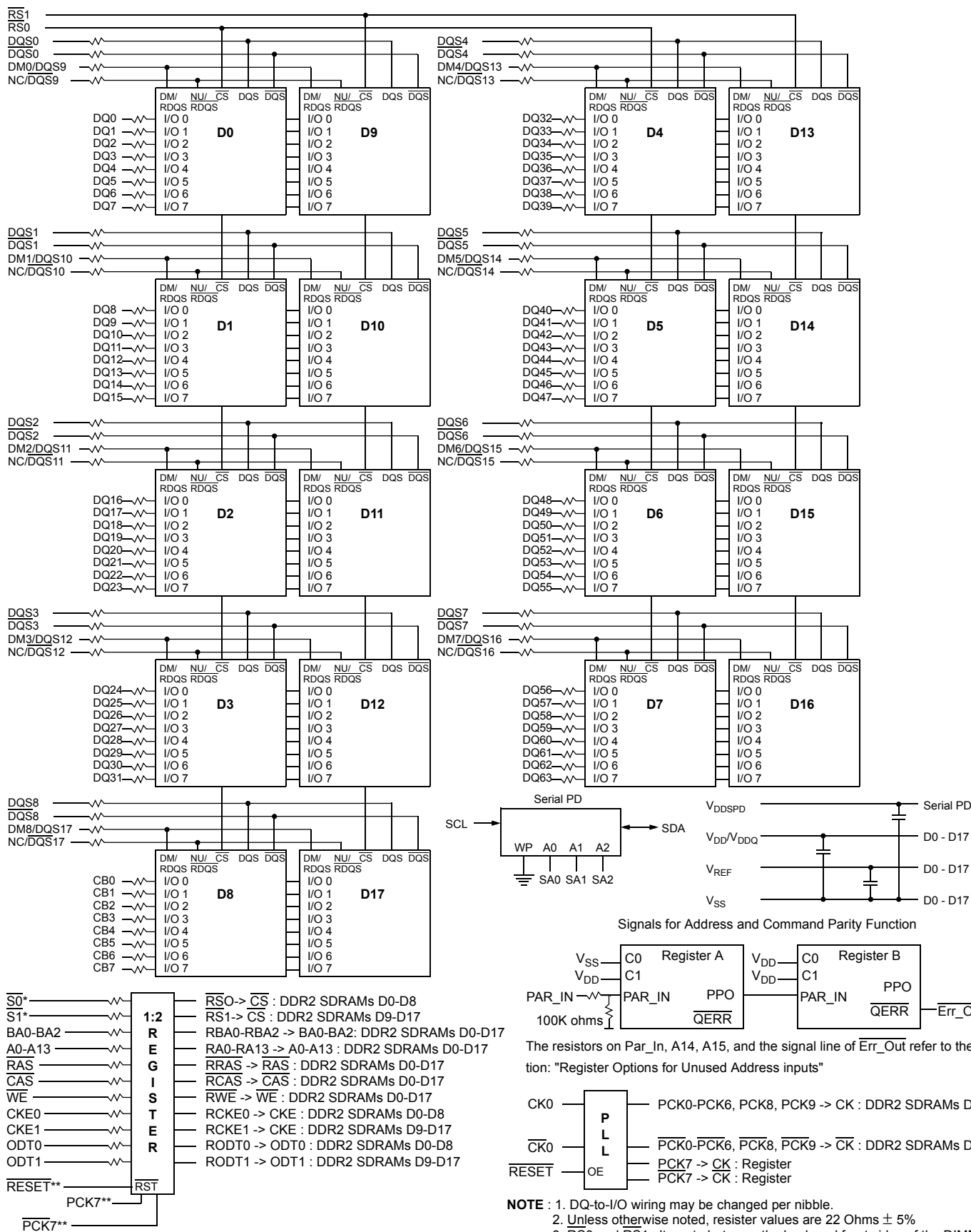


* S0 connects to DCS and VDD connects to CSR on the register. S1, CKE1 and ODT are NC.

- NOTE :**
1. DQ-to-I/O wiring may be changed within a byte.
 2. DQ/DQS/DM/CKE/S relationships must be maintained as shown.
 3. Unless otherwise noted, resistor values are 22 Ohms ± 5%



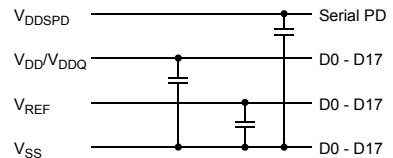
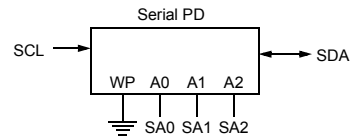
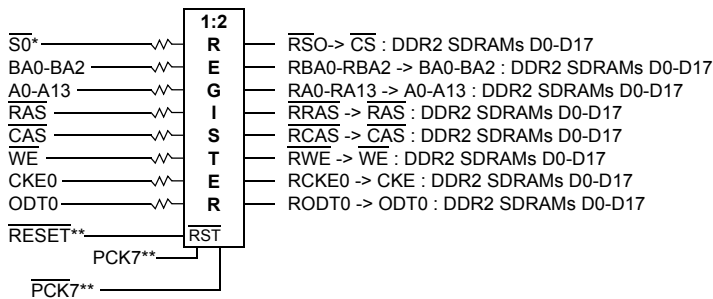
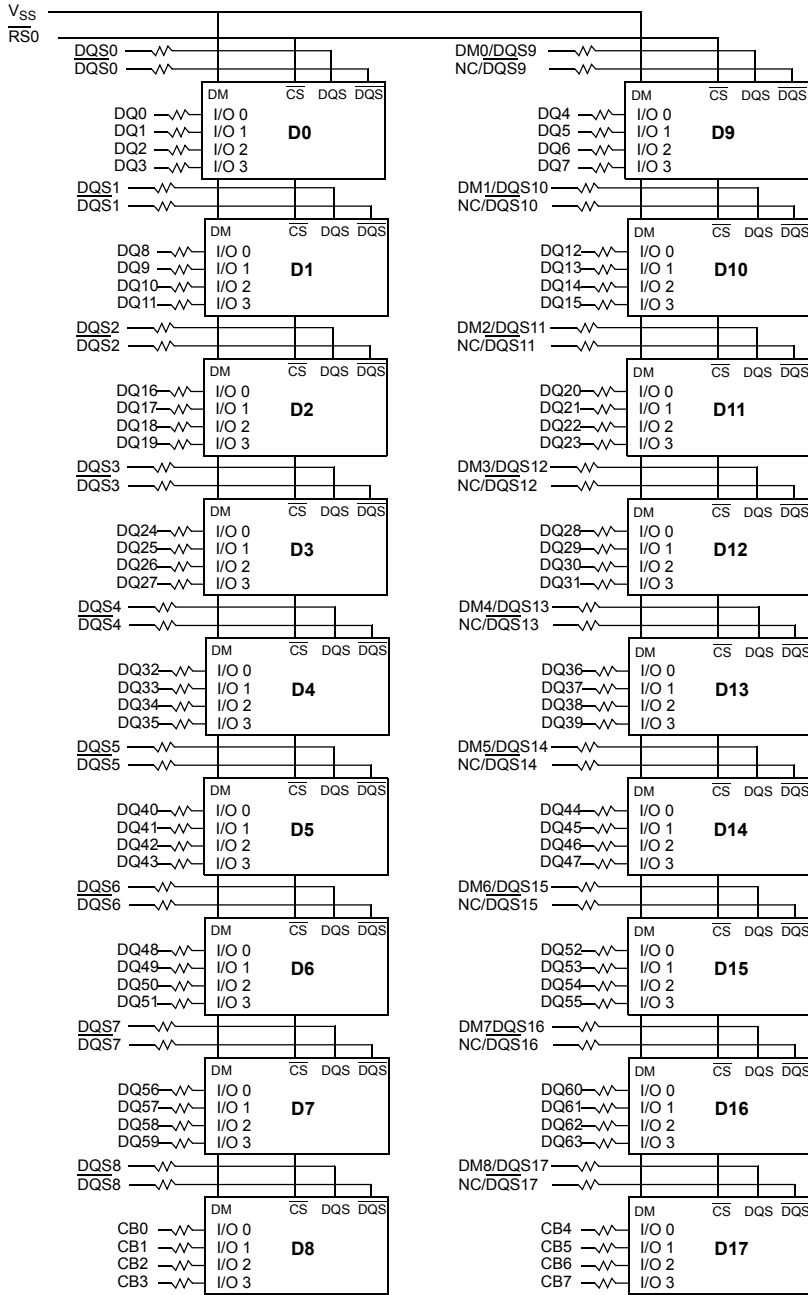
7.2 2GB, 256Mx72 Module - M393T5663FBA
(Populated as 2 ranks of x8 DDR2 SDRAMs)



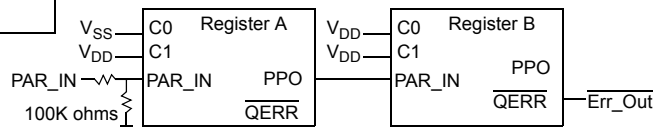
* S0 connects to DCS and S1 connects to CSR on a Register, S1 connects to DCS and S0 connects to CSR on another Register.
** RESET, PCK7 and PCK7 connects to both Registers. Other signals connect to one of two Registers.

7.3 2GB, 256Mx72 Module - M393T5660FBA

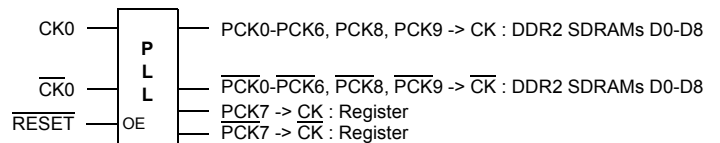
(Populated as 1 rank of x4 DDR2 SDRAMs)



Signals for Address and Command Parity Function



The resistors on Par_In, A14, A15, and the signal line of Err_Out refer to the section: "Register Options for Unused Address inputs"



NOTE : 1. DQ-to-I/O wiring may be changed per nibble.
2. Unless otherwise noted, resistor values are 22 Ohms ± 5%

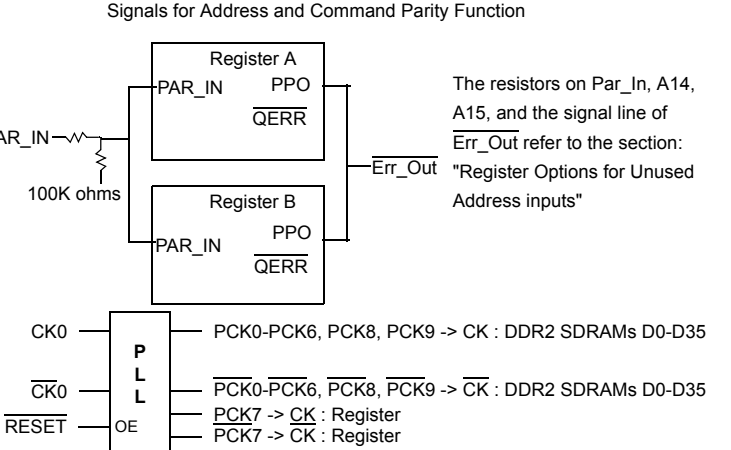
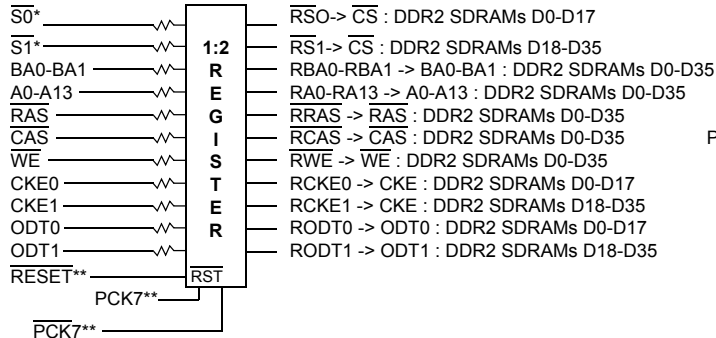
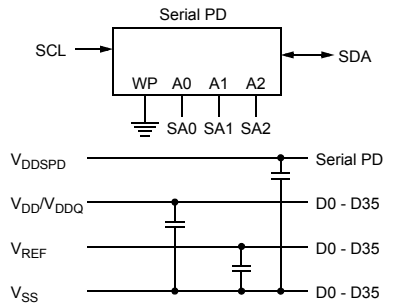
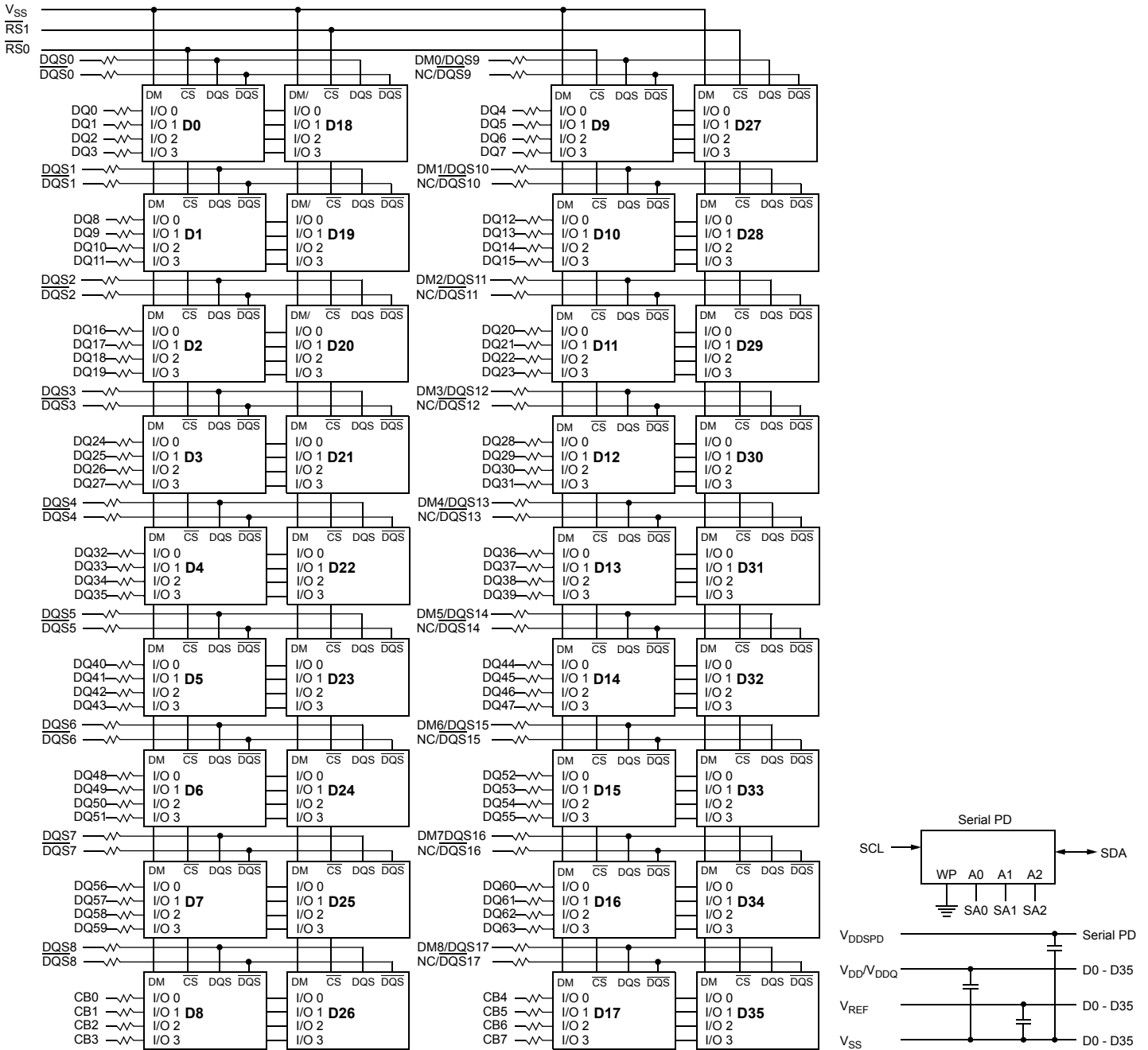
* S0 connects to DCS of Register1 and CSR of Register2. CSR of register 1 and DCS of register 2 connects to VDD.
** RESET, PCK7 and PCK7 connects to both Registers. Other signals connect to one of two Registers. S1, CKE1 and ODT1 are NC.



Registered DIMM

7.4 4GB, 512Mx72 Module - M393T5160FBA

(Populated as 2 ranks of x4 DDR2 SDRAMs)



The resistors on Par_In, A14, A15, and the signal line of Err_Out refer to the section: "Register Options for Unused Address inputs"

* S0 connects to DCS and S1 connects to CSR on a pair of Registers.
 S1 connects to DCS and S0 connects to CSR on another pair of Registers.
 ** RESET, PCK7 and PCK8 connects to all Registers.
 Other signals connect to one pair of four Registers.



8. Absolute Maximum DC Ratings

Symbol	Parameter	Rating	Units	NOTE
V_{DD}	Voltage on V_{DD} pin relative to V_{SS}	- 1.0 V ~ 2.3 V	V	1
V_{DDQ}	Voltage on V_{DDQ} pin relative to V_{SS}	- 0.5 V ~ 2.3 V	V	1
V_{DDL}	Voltage on V_{DDL} pin relative to V_{SS}	- 0.5 V ~ 2.3 V	V	1
V_{IN}, V_{OUT}	Voltage on any pin relative to V_{SS}	- 0.5 V ~ 2.3 V	V	1
T_{STG}	Storage Temperature	-55 to +100	°C	1, 2

NOTE :

- Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- Storage Temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JESD51-2 standard.

9. AC & DC Operating Conditions

9.1 Recommended DC Operating Conditions (SSTL - 1.8)

Symbol	Parameter	Rating			Units	NOTE
		Min.	Typ.	Max.		
V_{DD}	Supply Voltage	1.7	1.8	1.9	V	
V_{DDL}	Supply Voltage for DLL	1.7	1.8	1.9	V	4
V_{DDQ}	Supply Voltage for Output	1.7	1.8	1.9	V	4
V_{REF}	Input Reference Voltage	$0.49 \cdot V_{DDQ}$	$0.50 \cdot V_{DDQ}$	$0.51 \cdot V_{DDQ}$	mV	1,2
V_{TT}	Termination Voltage	$V_{REF} - 0.04$	V_{REF}	$V_{REF} + 0.04$	V	3

NOTE : There is no specific device V_{DD} supply voltage requirement for SSTL-1.8 compliance. However under all conditions V_{DDQ} must be less than or equal to V_{DD} .

- The value of V_{REF} may be selected by the user to provide optimum noise margin in the system. Typically the value of V_{REF} is expected to be about $0.5 \times V_{DDQ}$ of the transmitting device and V_{REF} is expected to track variations in V_{DDQ} .
- Peak to peak AC noise on V_{REF} may not exceed $\pm 2\% V_{REF}(DC)$.
- V_{TT} of transmitting device must track V_{REF} of receiving device.
- AC parameters are measured with V_{DD} , V_{DDQ} and V_{DDL} tied together.

9.2 Operating Temperature Condition

Symbol	Parameter	Rating	Units	NOTE
T _{OPER}	Operating Temperature	0 to 95	°C	1, 2

- NOTE :**
1. Operating Temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JESD51.2 standard.
 2. At 85 - 95 °C operation temperature range, doubling refresh commands in frequency to a 32ms period (tREFI=3.9 us) is required, and to enter to self refresh mode at this temperature range, an EMRS command is required to change internal refresh rate.

9.3 Input DC Logic Level

Symbol	Parameter	Min.	Max.	Units	NOTE
V _{IH} (DC)	DC input logic high	V _{REF} + 0.125	V _{DDQ} + 0.3	V	
V _{IL} (DC)	DC input logic low	- 0.3	V _{REF} - 0.125	V	

9.4 Input AC Logic Level

Symbol	Parameter	DDR2-667, DDR2-800		Units
		Min.	Max.	
V _{IH} (AC)	AC input logic high	V _{REF} + 0.200	-	V
V _{IL} (AC)	AC input logic low	-	V _{REF} - 0.200	V

9.5 AC Input Test Conditions

Symbol	Condition	Value	Units	NOTE
V _{REF}	Input reference voltage	0.5 * V _{DDQ}	V	1
V _{SWING} (MAX)	Input signal maximum peak to peak swing	1.0	V	1
SLEW	Input signal minimum slew rate	1.0	V/ns	2, 3

- NOTE :**
1. Input waveform timing is referenced to the input signal crossing through the V_{IH/IL}(AC) level applied to the device under test.
 2. The input signal minimum slew rate is to be maintained over the range from V_{REF} to V_{IH}(AC) min for rising edges and the range from V_{REF} to V_{IL}(AC) max for falling edges as shown in the below figure.
 3. AC timings are referenced with input waveforms switching from V_{IL}(AC) to V_{IH}(AC) on the positive transitions and V_{IH}(AC) to V_{IL}(AC) on the negative transitions.

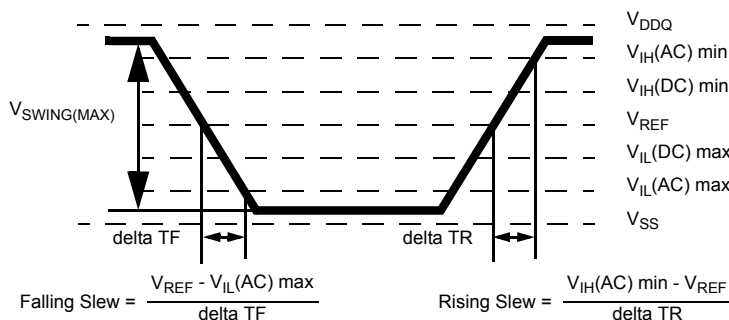


Figure 1. AC Input Test Signal Waveform

10. IDD Specification Parameters Definition

(IDD values are for full operating range of Voltage and Temperature)

Symbol	Proposed Conditions	Units	NOTE
IDD0	Operating one bank active-precharge current; tCK = tCK(IDD), tRC = tRC(IDD), tRAS = tRASmin(IDD); CKE is HIGH, \overline{CS} is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	
IDD1	Operating one bank active-read-precharge current; IOUT = 0mA; BL = 4, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRC = tRC(IDD), tRAS = tRASmin(IDD), tRCD = tRCD(IDD); CKE is HIGH, \overline{CS} is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W	mA	
IDD2P	Precharge power-down current; All banks idle; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	mA	
IDD2Q	Precharge quiet standby current; All banks idle; tCK = tCK(IDD); CKE is HIGH, \overline{CS} is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	mA	
IDD2N	Precharge standby current; All banks idle; tCK = tCK(IDD); CKE is HIGH, \overline{CS} is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	
IDD3P	Active power-down current; All banks open; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	Fast PDN Exit MRS(12) = 0	mA
		Slow PDN Exit MRS(12) = 1	mA
IDD3N	Active standby current; All banks open; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, \overline{CS} is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	
IDD4W	Operating burst write current; All banks open, Continuous burst writes; BL = 4, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, \overline{CS} is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	
IDD4R	Operating burst read current; All banks open, Continuous burst reads, IOUT = 0mA; BL = 4, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, \overline{CS} is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W	mA	
IDD5B	Burst auto refresh current; tCK = tCK(IDD); Refresh command at every tRFC(IDD) interval; CKE is HIGH, \overline{CS} is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	
IDD6	Self refresh current; CK and \overline{CK} at 0V; CKE ≤ 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING	Normal	mA
		Low Power	mA
IDD7	Operating bank interleave read current; All bank interleaving reads, IOUT = 0mA; BL = 4, CL = CL(IDD), AL = tRCD(IDD)-1*tCK(IDD); tCK = tCK(IDD), tRC = tRC(IDD), tRRD = tRRD(IDD), tFAW = tFAW(IDD), tRCD = 1*tCK(IDD); CKE is HIGH, \overline{CS} is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data pattern is same as IDD4R; Refer to the following page for detailed timing conditions	mA	

11. Operating Current Table :

11.1 M393T2863FBA : 1GB(128Mx8 *9) Module

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	405	405	387	mA	
IDD1	459	459	432	mA	
IDD2P	90	90	90	mA	
IDD2Q	180	180	180	mA	
IDD2N	225	225	216	mA	
IDD3P-F	207	207	198	mA	
IDD3P-S	180	180	180	mA	
IDD3N	333	333	315	mA	
IDD4W	648	648	585	mA	
IDD4R	720	720	630	mA	
IDD5B	945	945	900	mA	
IDD6 ¹	90	90	90	mA	
IDD7	1,440	1,440	1,305	mA	

NOTE :

1. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.2 M393T2863FBA : 1GB(128Mx8 *9) Module - considering Register and PLL current value

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL=6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	795	995	887	mA	
IDD1	899	1,099	982	mA	
IDD2P	550	570	530	mA	
IDD2Q	620	710	640	mA	
IDD2N	585	705	636	mA	
IDD3P-F	637	757	668	mA	
IDD3P-S	610	730	650	mA	
IDD3N	683	873	785	mA	
IDD4W	1,028	1,168	1,035	mA	
IDD4R	1,180	1,310	1,140	mA	
IDD5B	1,325	1,615	1,450	mA	
IDD6 ¹	90	90	90	mA	
IDD7	1,990	2,130	1,885	mA	

NOTE :

1. IDD6 = DRAM current + standby current of PLL and Register

2. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.3 M393T5663FBA : 2GB(128Mx8 *18) Module

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	630	630	603	mA	
IDD1	684	684	648	mA	
IDD2P	180	180	180	mA	
IDD2Q	360	360	360	mA	
IDD2N	450	450	432	mA	
IDD3P-F	414	414	396	mA	
IDD3P-S	360	360	360	mA	
IDD3N	558	558	531	mA	
IDD4W	873	873	801	mA	
IDD4R	945	945	846	mA	
IDD5B	1,170	1,170	1,116	mA	
IDD6 ¹	180	180	180	mA	
IDD7	1,665	1,665	1,521	mA	

NOTE :

1. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.4 M393T5663FBA : 2GB(128Mx8 *18) Module - considering Register and PLL current value

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL=6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	1,320	1,320	1,193	mA	
IDD1	1,454	1,454	1,308	mA	
IDD2P	820	820	760	mA	
IDD2Q	1,070	1,070	980	mA	
IDD2N	1,020	1,020	932	mA	
IDD3P-F	1,144	1,144	1,026	mA	
IDD3P-S	1,090	1,090	990	mA	
IDD3N	1,118	1,118	1,021	mA	
IDD4W	1,523	1,523	1,361	mA	
IDD4R	1,735	1,735	1,526	mA	
IDD5B	2,000	2,000	1,796	mA	
IDD6 ¹	180	180	180	mA	
IDD7	2,695	2,695	2,391	mA	

NOTE :

1. IDD6 = DRAM current + standby current of PLL and Register

2. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.5 M393T5660FBA : 2GB(256Mx4 *18) Module

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	810	810	774	mA	
IDD1	918	918	864	mA	
IDD2P	180	180	180	mA	
IDD2Q	360	360	360	mA	
IDD2N	450	450	432	mA	
IDD3P-F	414	414	396	mA	
IDD3P-S	360	360	360	mA	
IDD3N	666	666	630	mA	
IDD4W	1,206	1,206	1,080	mA	
IDD4R	1,368	1,368	1,188	mA	
IDD5B	1,890	1,890	1,800	mA	
IDD6 ¹	180	180	180	mA	
IDD7	2,808	2,808	2,538	mA	

NOTE :

1. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.6 M393T5660FBA : 2GB(256Mx4 *18) Module - considering Register and PLL current value

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL=6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	1,500	1,500	1,364	mA	
IDD1	1,688	1,688	1,524	mA	
IDD2P	820	820	760	mA	
IDD2Q	1,070	1,070	980	mA	
IDD2N	1,020	1,020	932	mA	
IDD3P-F	1,144	1,144	1,026	mA	
IDD3P-S	1,090	1,090	990	mA	
IDD3N	1,226	1,226	1,120	mA	
IDD4W	1,856	1,856	1,640	mA	
IDD4R	2,158	2,158	1,868	mA	
IDD5B	2,720	2,720	2,480	mA	
IDD6 ¹	180	180	180	mA	
IDD7	3,838	3,838	3,408	mA	

NOTE :

1. IDD6 = DRAM current + standby current of PLL and Register

2. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.7 M393T5160FBA : 4GB(256Mx4 *36) Module

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	1,260	1,260	1,206	mA	
IDD1	1,368	1,368	1,296	mA	
IDD2P	360	360	360	mA	
IDD2Q	720	720	720	mA	
IDD2N	900	900	864	mA	
IDD3P-F	828	828	792	mA	
IDD3P-S	720	720	720	mA	
IDD3N	1,116	1,116	1,062	mA	
IDD4W	1,656	1,656	1,512	mA	
IDD4R	1,818	1,818	1,620	mA	
IDD5B	2,340	2,340	2,232	mA	
IDD6 ¹	360	360	360	mA	
IDD7	3,258	3,258	2,970	mA	

NOTE :

1. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

11.8 M393T5160FBA : 4GB(256Mx4 *36) Module - considering Register and PLL current value

(TA=0°C, V_{DD}= 1.9V)

Symbol	800@CL=5	800@CL=6	667@CL=5	Units	NOTE
	CE7	CF7	CE6		
IDD0	2,280	2,280	2,076	mA	
IDD1	2,528	2,528	2,296	mA	
IDD2P	1,310	1,310	1,220	mA	
IDD2Q	1,780	1,780	1,640	mA	
IDD2N	1,700	1,700	1,564	mA	
IDD3P-F	1,918	1,918	1,732	mA	
IDD3P-S	1,810	1,810	1,660	mA	
IDD3N	1,906	1,906	1,752	mA	
IDD4W	2,646	2,646	2,362	mA	
IDD4R	2,908	2,908	2,560	mA	
IDD5B	3,560	3,560	3,232	mA	
IDD6 ¹	360	360	360	mA	
IDD7	4,968	4,968	4,420	mA	

NOTE :

1. IDD6 = DRAM current + standby current of PLL and Register

2. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading cap.

12. Input/Output Capacitance

(V_{DD}=1.8V, V_{DDQ}=1.8V, TA=25°C)

Parameter	Sym.	Min	Max	Min	Max	Min	Max	Min	Max	Units
Part-Number		M393T2863FBA		M393T5663FBA		M393T5660FBA		M393T5160FBA		
Input capacitance, CK and \overline{CK}	CCK	-	11	-	11	-	11	-	11	pF
Input capacitance, CKE and \overline{CS}	CI1	-	12	-	12	-	12	-	12	
Input capacitance, Address, RAS, CAS, WE	CI2	-	12	-	12	-	12	-	12	
Input/output capacitance, DQ, DM, DQS, DQS	CIO	-	10	-	10	-	10	-	10	

NOTE : DM is internally loaded to match DQ and DQS identically.

13. Electrical Characteristics & AC Timing for DDR2-800/667

(0°C ≤ T_{OPER} ≤ 95°C, V_{DDQ} = 1.8V ± 0.1V, V_{DD} = 1.8V ± 0.1V)

13.1 Refresh Parameters by Device Density

Parameter	Symbol	256Mb	512Mb	1Gb	2Gb	4Gb	Units	
Refresh to active/Refresh command time	tRFC	75	105	127.5	195	327.5	ns	
Average periodic refresh interval	tREFI	0 °C ≤ T _{CASE} ≤ 85°C	7.8	7.8	7.8	7.8	7.8	μs
		85 °C < T _{CASE} ≤ 95°C	3.9	3.9	3.9	3.9	3.9	μs

13.2 Speed Bins and CL, tRCD, tRP, tRC and tRAS for Corresponding Bin

Speed	DDR2-800(E7)		DDR2-800(F7)		DDR2-667(E6)		Units
Bin(CL - tRCD - tRP)	5 - 5 - 5		6 - 6 - 6		5 - 5 - 5		
Parameter	min	max	min	max	min	max	
tCK, CL=3	5	8	-	-	5	8	ns
tCK, CL=4	3.75	8	3.75	8	3.75	8	ns
tCK, CL=5	2.5	8	3	8	3	8	ns
tCK, CL=6	-	-	2.5	8	-	-	ns
tRCD	12.5	-	15	-	15	-	ns
tRP	12.5	-	15	-	15	-	ns
tRC	57.5	-	60	-	60	-	ns
tRAS	45	70000	45	70000	45	70000	ns

13.3 Timing Parameters by Speed Grade

(Refer to notes for informations related to this table at the component datasheet)

Parameter	Symbol	DDR2-800		DDR2-667		Units	NOTE
		min	max	min	max		
DQ output access time from $\overline{CK}/\overline{CK}$	tAC	-400	400	- 450	450	ps	40
DQS output access time from $\overline{CK}/\overline{CK}$	tDQSCK	-350	350	- 400	400	ps	40
Average clock HIGH pulse width	tCH(avg)	0.48	0.52	0.48	0.52	tCK(avg)	35,36
Average clock LOW pulse width	tCL(avg)	0.48	0.52	0.48	0.52	tCK(avg)	35,36
CK half pulse period	tHP	Min(tCL(abs), tCH(abs))	x	Min(tCL(abs), tCH(abs))	x	ps	37
Average clock period	tCK(avg)	2500	8000	3000	8000	ps	35,36
DQ and DM input hold time	tDH(base)	125	x	175	x	ps	6,7,8,21,28,31
DQ and DM input setup time	tDS(base)	50	x	100	x	ps	6,7,8,20,28,31
Control & Address input pulse width for each input	tIPW	0.6	x	0.6	x	tCK(avg)	
DQ and DM input pulse width for each input	tDIPW	0.35	x	0.35	x	tCK(avg)	
Data-out high-impedance time from $\overline{CK}/\overline{CK}$	tHZ	x	tAC(max)	x	tAC(max)	ps	18,40
DQS/ \overline{DQS} low-impedance time from $\overline{CK}/\overline{CK}$	tLZ(DQS)	tAC(min)	tAC(max)	tAC(min)	tAC(max)	ps	18,40
DQ low-impedance time from $\overline{CK}/\overline{CK}$	tLZ(DQ)	2* tAC(min)	tAC(max)	2* tAC(min)	tAC(max)	ps	18,40
DQS-DQ skew for DQS and associated DQ signals	tDQSQ	x	200	x	240	ps	13
DQ hold skew factor	tQHS	x	300	x	340	ps	38
DQ/DQS output hold time from DQS	tQH	tHP - tQHS	x	tHP - tQHS	x	ps	39
DQS latching rising transitions to associated clock edges	tDQSS	- 0.25	0.25	-0.25	0.25	tCK(avg)	30
DQS input HIGH pulse width	tDQSH	0.35	x	0.35	x	tCK(avg)	
DQS input LOW pulse width	tDQSL	0.35	x	0.35	x	tCK(avg)	
DQS falling edge to CK setup time	tDSS	0.2	x	0.2	x	tCK(avg)	30
DQS falling edge hold time from CK	tDSH	0.2	x	0.2	x	tCK(avg)	30
Mode register set command cycle time	tMRD	2	x	2	x	nCK	
MRS command to ODT update delay	tMOD	0	12	0	12	ns	32
Write postamble	tWPST	0.4	0.6	0.4	0.6	tCK(avg)	10
Write preamble	tWPRE	0.35	x	0.35	x	tCK(avg)	
Address and control input hold time	tIH(base)	250	x	275	x	ps	5,7,9,23,29
Address and control input setup time	tIS(base)	175	x	200	x	ps	5,7,9,22,29
Read preamble	tRPRE	0.9	1.1	0.9	1.1	tCK(avg)	19,41
Read postamble	tRPST	0.4	0.6	0.4	0.6	tCK(avg)	19,42
Activate to activate command period for 1KB page size products	tRRD	7.5	x	7.5	x	ns	4,32
Activate to activate command period for 2KB page size products	tRRD	10	x	10	x	ns	4,32

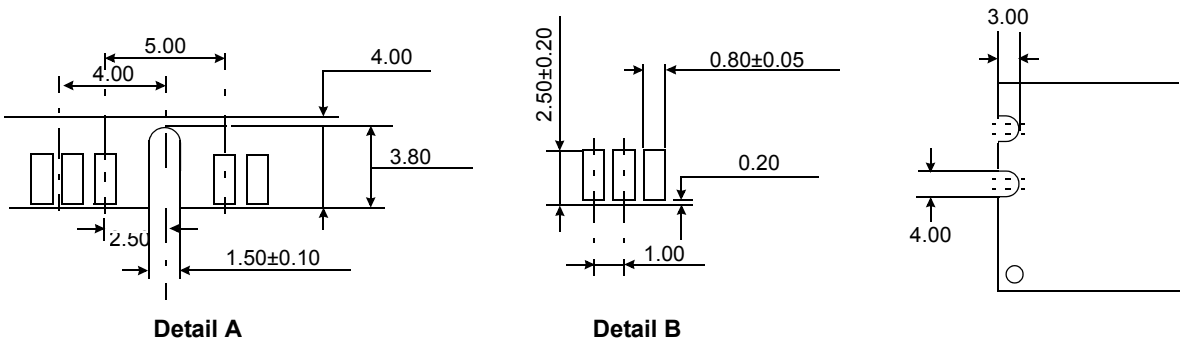
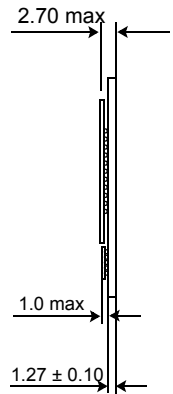
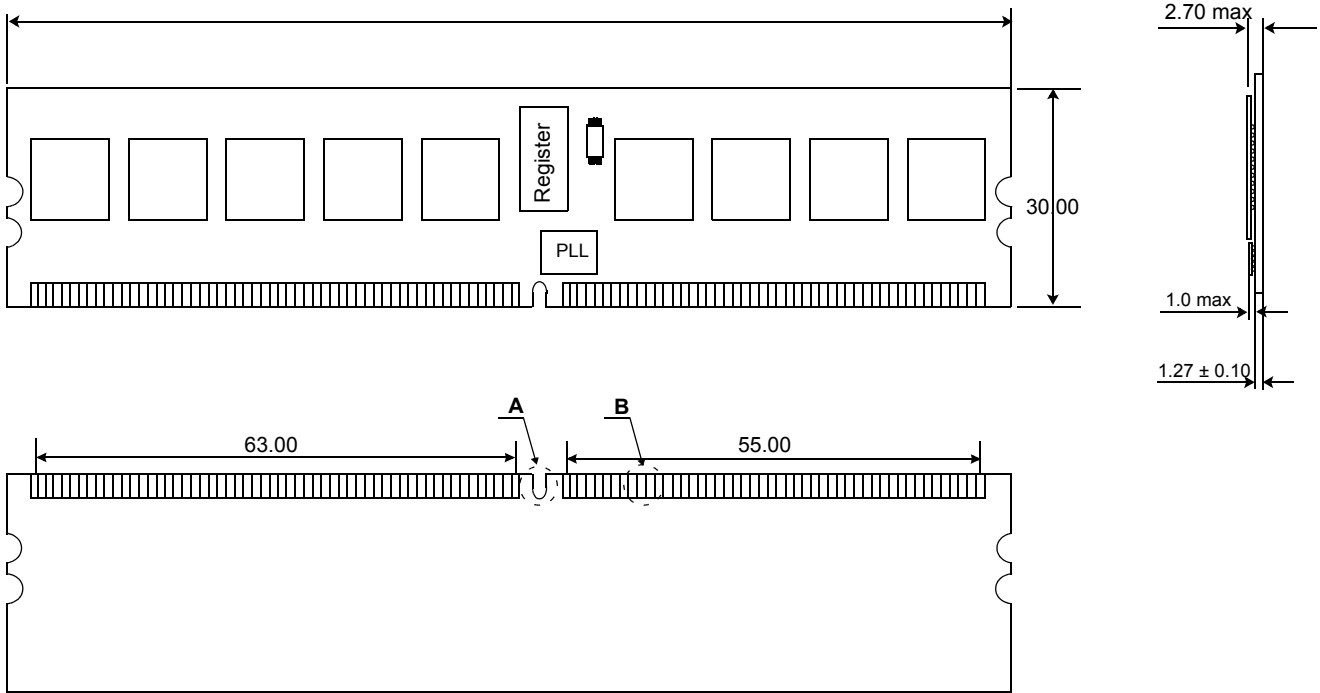
Parameter	Symbol	DDR2-800		DDR2-667		Units	NOTE
		min	max	min	max		
Four Activate Window for 1KB page size products	tFAW	35	x	37.5	x	ns	32
Four Activate Window for 2KB page size products	tFAW	45	x	50	x	ns	32
CAS to $\overline{\text{CAS}}$ command delay	tCCD	2	x	2	x	nCK	
Write recovery time	tWR	15	x	15	x	ns	32
Auto precharge write recovery + precharge time	tDAL	WR + tnRP	x	WR + tnRP	x	nCK	33
Internal write to read command delay	tWTR	7.5	x	7.5	x	ns	24,32
Internal read to precharge command delay	tRTP	7.5	x	7.5	x	ns	3,32
Exit self refresh to a non-read command	tXSNR	tRFC + 10	x	tRFC + 10	x	ns	32
Exit self refresh to a read command	tXSRD	200	x	200	x	nCK	
Exit precharge power down to any command	tXP	2	x	2	x	nCK	
Exit active power down to read command	tXARD	2	x	2	x	nCK	1
Exit active power down to read command (slow exit, lower power)	tXARDS	8 - AL	x	7 - AL	x	nCK	1,2
CKE minimum pulse width (HIGH and LOW pulse width)	tCKE	3	x	3	x	nCK	27
ODT turn-on delay	tAOND	2	2	2	2	nCK	16
ODT turn-on	tAON	tAC(min)	tAC(max)+0.7	tAC(min)	tAC(max)+0.7	ns	6,16,40
ODT turn-on (Power-Down mode)	tAONPD	tAC(min)+2	2*tCK(avg)+tAC(max)+1	tAC(min)+2	2*tCK(avg)+tAC(max)+1	ns	
ODT turn-off delay	tAOFD	2.5	2.5	2.5	2.5	nCK	17,45
ODT turn-off	tAOF	tAC(min)	tAC(max)+0.6	tAC(min)	tAC(max)+0.6	ns	17,43,45
ODT turn-off (Power-Down mode)	tAOFPD	tAC(min)+2	2.5*tCK(avg)+tAC(max)+1	tAC(min)+2	2.5*tCK(avg)+tAC(max)+1	ns	
ODT to power down entry latency	tANPD	3	x	3	x	nCK	
ODT power down exit latency	tAXPD	8	x	8	x	nCK	
OCD drive mode output delay	tOIT	0	12	0	12	ns	32
Minimum time clocks remains ON after CKE asynchronously drops LOW	tDelay	tIS+tCK(avg)+tIH	x	tIS+tCK(avg)+tIH	x	ns	15

14. Physical Dimensions :

14.1 128Mbx8 based 128Mx72 Module (1 Rank)

- M393T2863FBA

Units : Millimeters

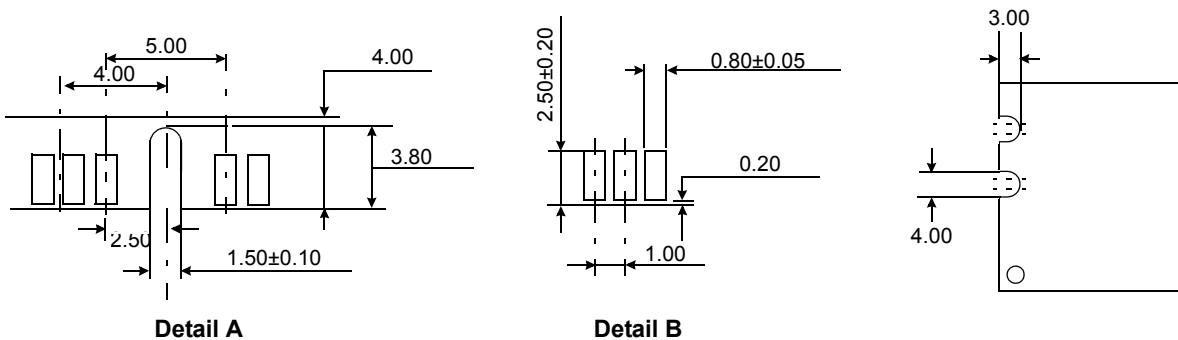
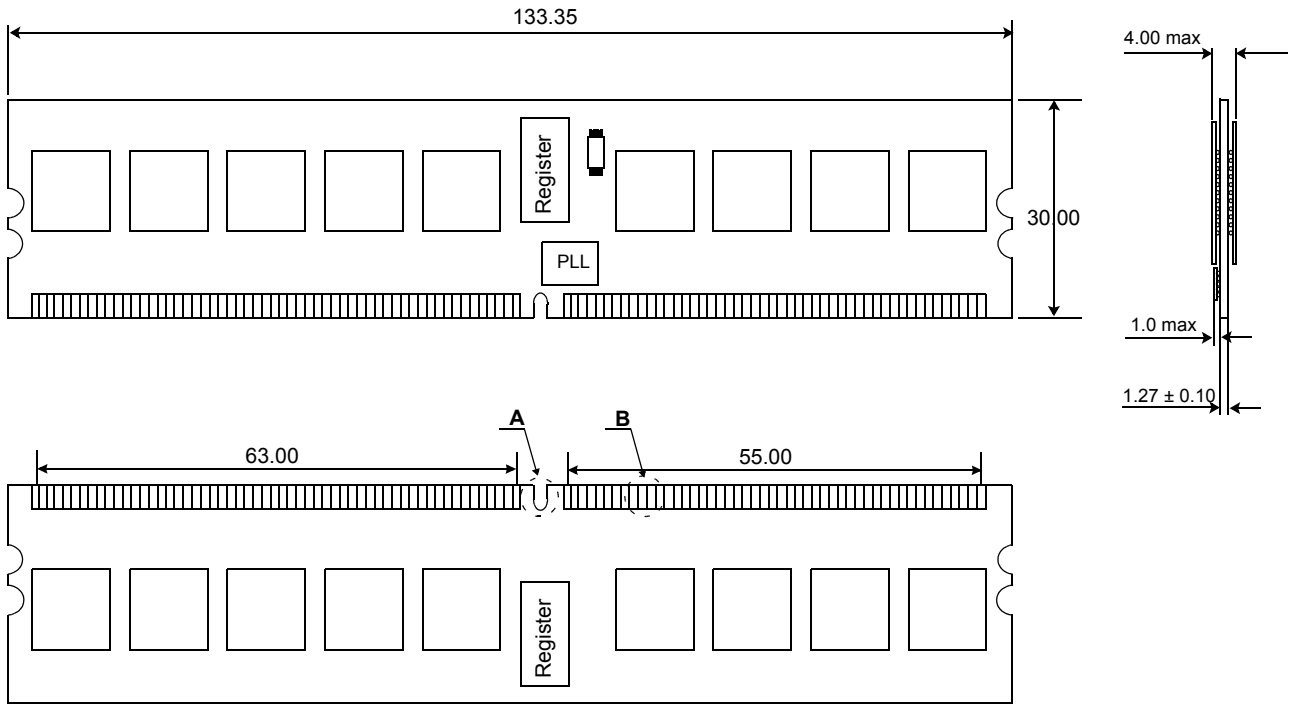


The used device is 128M x8 DDR2 SDRAM, Flip-chip.
DDR2 SDRAM Part NO : K4T1G084QF

14.2 128Mbx8/256Mbx4 based 256Mx72 Module (2 Ranks / 1 Rank)

- M393T5663FBA/M393T5660FBA

Units : Millimeters

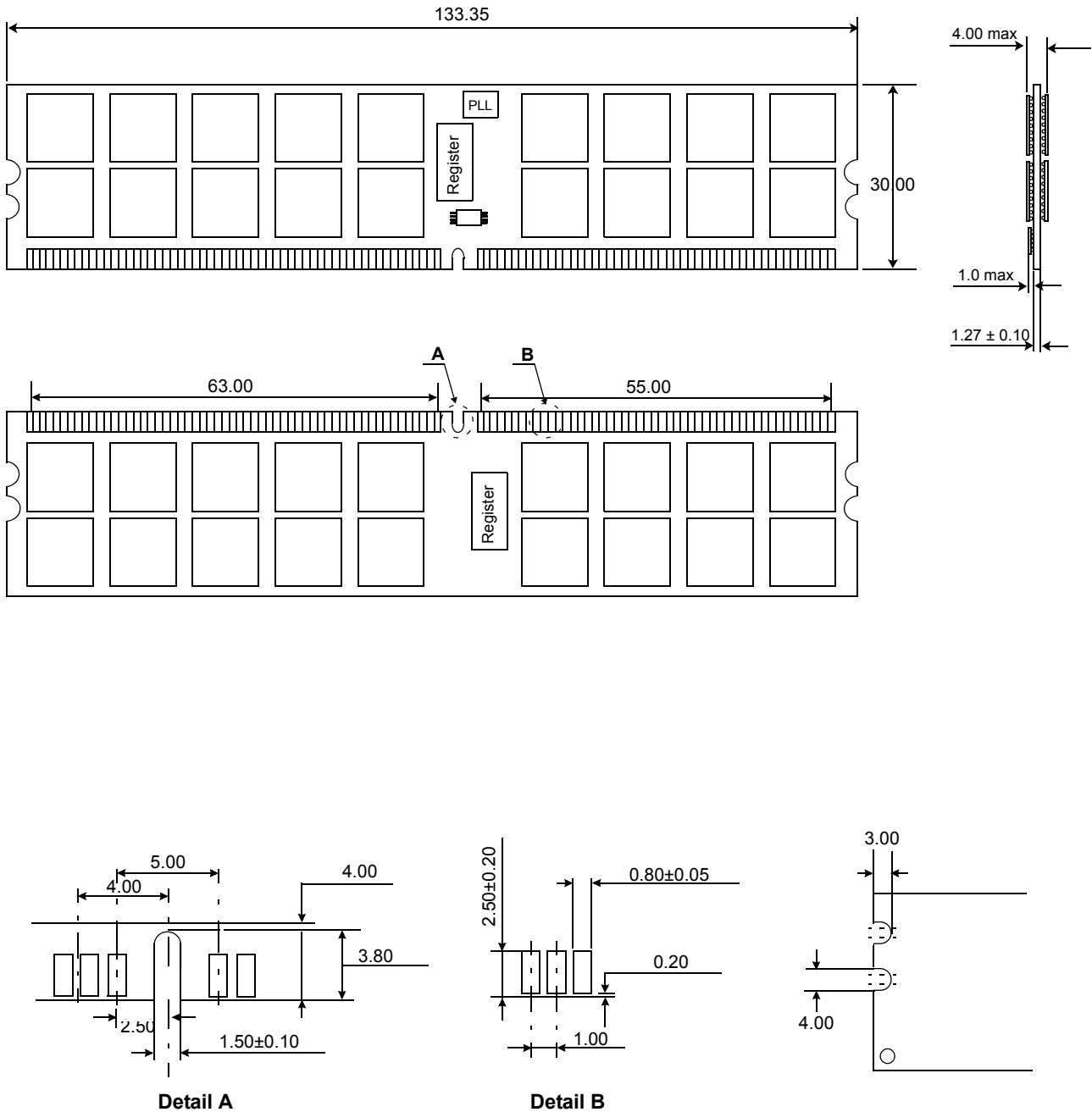


The used device is 128M x8 / 256M x4 DDR2 SDRAM, Flip-chip.
DDR2 SDRAM Part NO : K4T1G084QF / K4T1G044QF

14.3 256Mbx4 based 512Mx72 Module (2 Ranks)

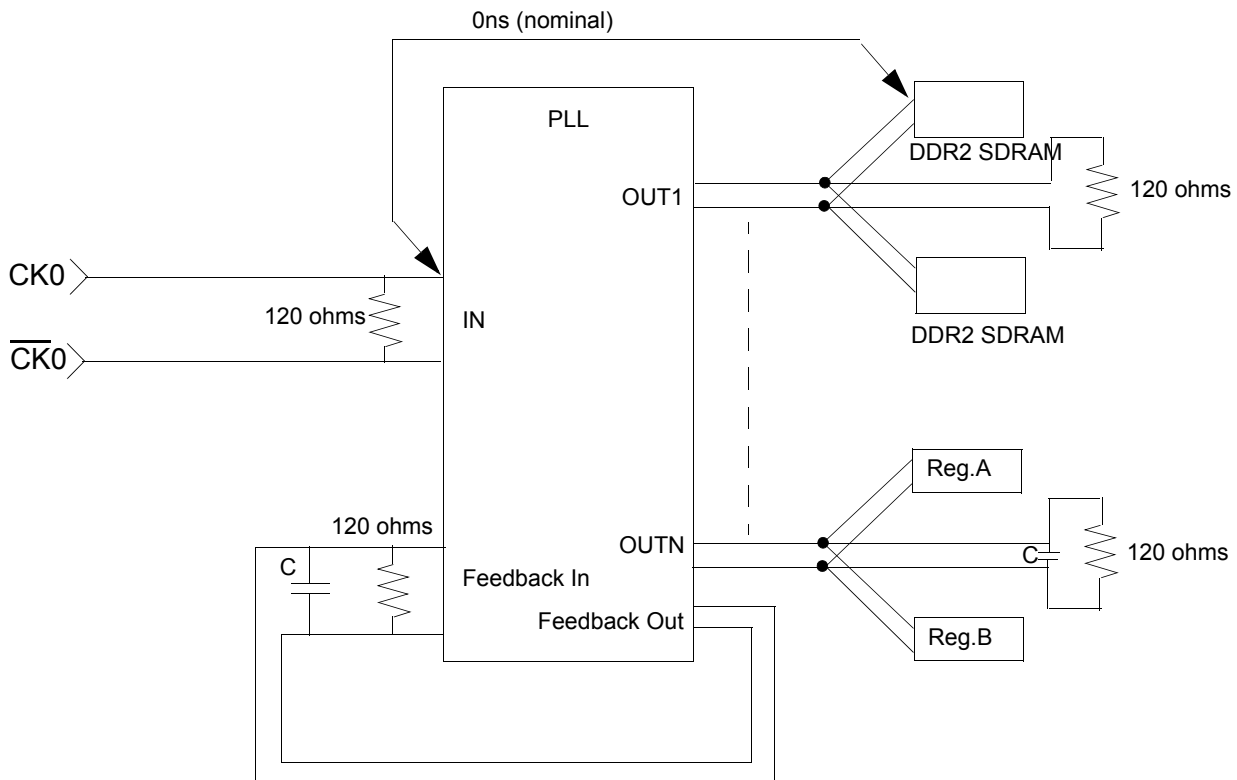
- M393T5160FBA

Units : Millimeters



The used device is 256M x4 DDR2 SDRAM, Flip-chip.
DDR2 SDRAM Part NO : K4T1G044QF

15. 240 Pin DDR2 Registered DIMM Clock Topology

**NOTE :**

1. The clock delay from the input of the PLL clock to the input of any DDR2 SDRAM or register will be set to 0ns (nominal).
2. Input, output, and feedback clock lines are terminated from line to line as shown, and not from line to ground.
3. Only one PLL output is shown per output type. Any additional PLL outputs will be wired in a similar manner.
4. Termination resistors for the PLL feedback path clocks are located as close to the input pin of the PLL as possible.